Abstracts

New Heterodyne Receiver Head

T. Hayasaka, M. Noguchi and K. Sakamoto. "New Heterodyne Receiver Head." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 144-146.

Low noise GaAs FET amplifiers are widely employed for heterodyne receiver heads in order to improve their noise figure. In the new heterodyne receiver head discussed here, the low noise GaAs FET amplifier used to improve the noise figure is also used for oscillation of the local signal without any degradation of the transmission characteristics, so that the local oscillator, used in a conventional heterodyne receiver head can be dispensed with. The configuration of the new heterodyne receiver head is a very effective low cost, low power consumption design for a MIC receiver head.

☐ Return to main document.

Click on title for a complete paper.